

NMOS 16K (2K x 8) UV EPROM

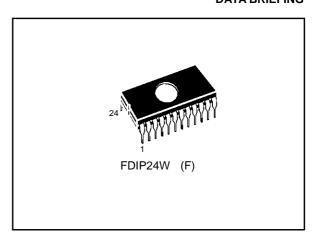
DATA BRIEFING

- 2048 x 8 ORGANIZATION
- 525mW Max ACTIVE POWER, 132mW Max STANDBY POWER
- ACCESS TIME:
 - M2716-1 is 350ns
 - M2716 is 450ns
- SINGLE 5V SUPPLY VOLTAGE
- STATIC-NO CLOCKS REQUIRED
- INPUTS and OUTPUTS TTL COMPATIBLE DURING BOTH READ and PROGRAM MODES
- THREE-STATE OUTPUT with TIED-OR-CAPABILITY
- EXTENDED TEMPERATURE RANGE
- PROGRAMMING VOLTAGE: 25V

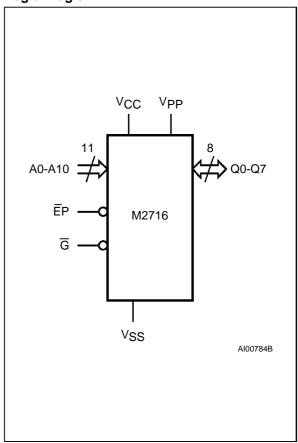
DESCRIPTION

The M2716 is a 16,384 bit UV erasable and electrically programmable memory EPROM, ideally suited for applications where fast turn around and pattern experimentation are important requirements

The M2716 is housed in a 24 pin Window Ceramic Frit-Seal Dual-in-Line package. The transparent lid allows the user to expose the chip to ultraviolet light to erase the bit pattern. A new pattern can then be written to the device by following the programming procedure.

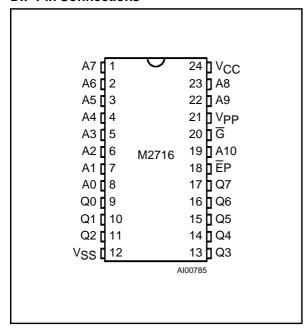


Logic Diagram



B2716/407 1/2

DIP Pin Connections



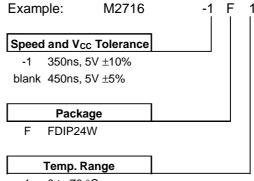
Signal Names

A0 - A10	Address Inputs
Q0 - Q7	Data Outputs
ĒΡ	Chip Enable / Program
G	Output Enable
V _{PP}	Program Supply
Vcc	Supply Voltage
V _{SS}	Ground

Ordering Information Scheme

For a list of available options refer to the current Memory Shortform catalogue.

For further information on any aspect of this device, please contact the SGS-THOMSON Sales Office nearest to you.



- 1 0 to 70 °C
- 6 -40 to 85 °C